

TRIPLE 3-INPUT NAND GATE

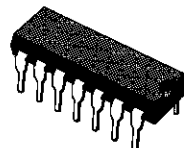
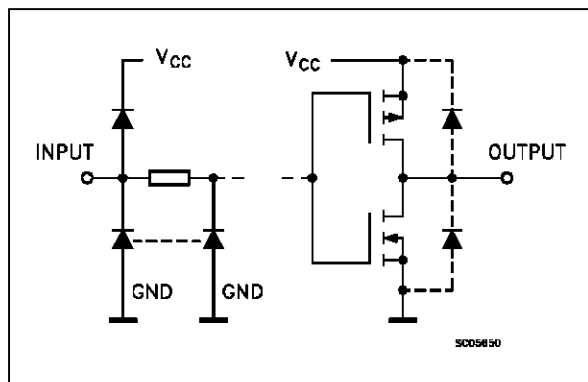
- HIGH SPEED
 $t_{PD} = 11 \text{ ns (TYP.) AT } V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION
 $I_{CC} = 1 \mu\text{A (MAX.) AT } T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS
 $V_{IH} = 2 \text{ V (MIN.) } V_{IL} = 0.8 \text{ V (MAX.)}$
- OUTPUT DRIVE CAPABILITY
10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = I_{OL} = 4 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- PIN AND FUNCTION COMPATIBLE WITH
54/74LS10

DESCRIPTION

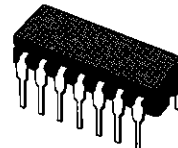
The M54/74HCT10 is a high speed CMOS TRIPLE 3-INPUT NAND GATE fabricated with silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

This integrated circuit has input and output characteristics that are fully compatible with 54/74 LSTTL logic families. M54/74HCT devices are designed to directly interface HSC²MOS systems with TTL and NMOS components. They are also plug in replacements for LSTTL devices giving a reduction of power consumption.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



B1R
(Plastic Package)



F1R
(Ceramic Package)



M1R
(Micro Package)

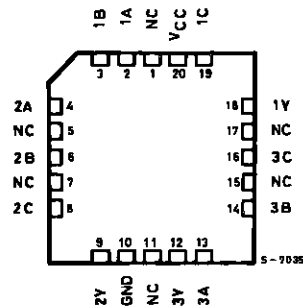
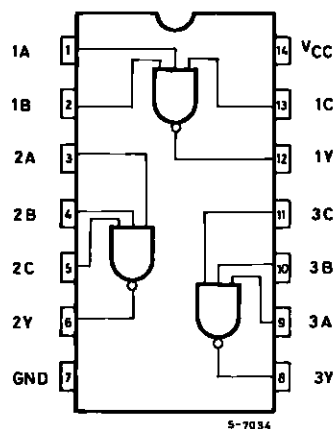


C1R
(Chip Carrier)

ORDER CODES :

M54HCT10F1R	M74HCT10M1R
M74HCT10B1R	M74HCT10C1R

PIN CONNECTIONS (top view)



NC =
No Internal
Connection

M54/M74HCT10

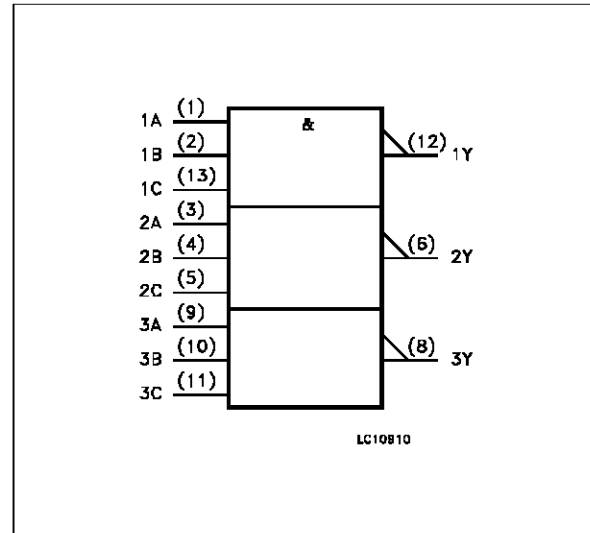
TRUTH TABLE

A	B	C	Y
L	X	X	H
X	L	X	H
X	X	L	H
H	H	H	L

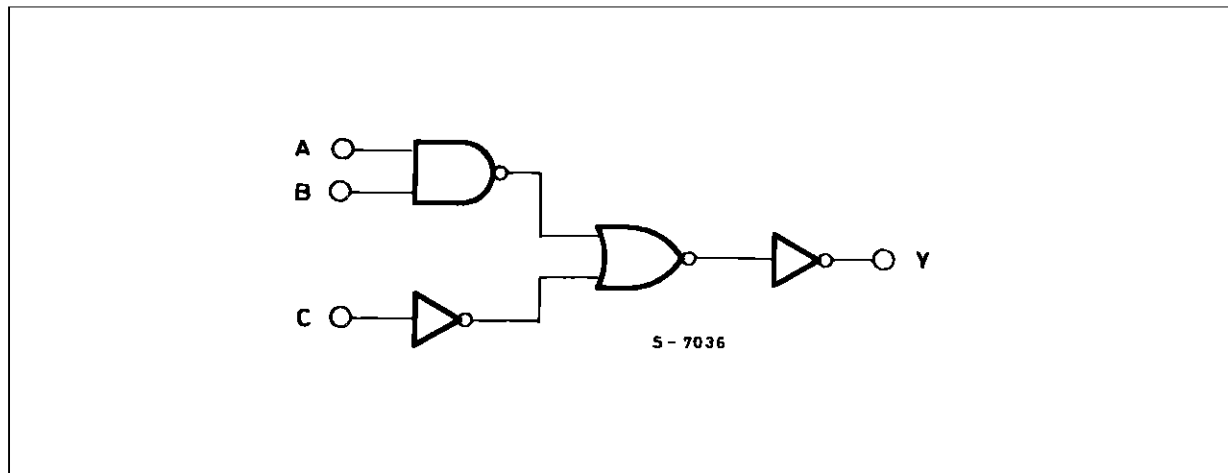
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A to 3A	Data Inputs
2, 4, 10	1B to 3B	Data Inputs
13, 5, 11	1C to 3C	Data Inputs
12, 6, 8	1Y to 3Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



SCHEMATIC CIRCUIT (Per Gate)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ± 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	$^{\circ}\text{C}$ $^{\circ}\text{C}$
t_r, t_f	Input Rise and Fall Time ($V_{CC} = 4.5$ to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions				Value						Unit
		V _{CC} (V)			T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	4.5 to 5.5			2.0			2.0		2.0		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5					0.8		0.8		0.8	V
V _{OH}	High Level Output Voltage	4.5	V _I = V _{IH} or V _{IL}	I _O =-20 μA	4.4	4.5		4.4		4.4		V
				I _O =-4.0 mA	4.18	4.31		4.13		4.10		
V _{OL}	Low Level Output Voltage	4.5	V _I = V _{IH} or V _{IL}	I _O = 20 μA		0.0	0.1		0.1		0.1	V
				I _O = 4.0 mA		0.17	0.26		0.33		0.4	
I _I	Input Leakage Current	5.5	V _I = V _{CC} or GND				±0.1		±1		±1	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND				1		10		20	μA
ΔI _{CC}	Additional worst case supply current	5.5	Per Input pin V _I = 0.5V or V _I = 2.4V Other Inputs at V _{CC} or GND I _O = 0				2.0		2.9		3.0	mA

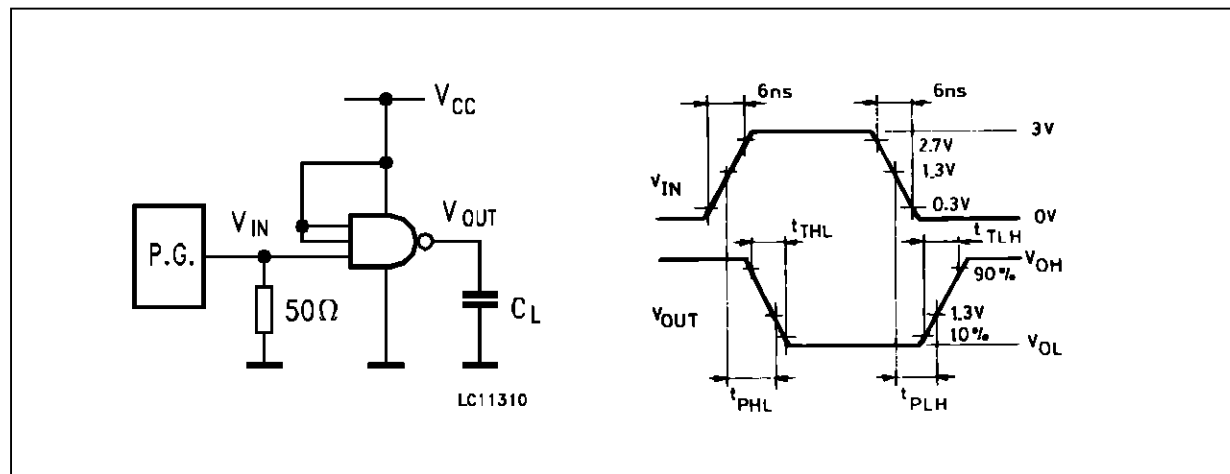
M54/M74HCT10

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

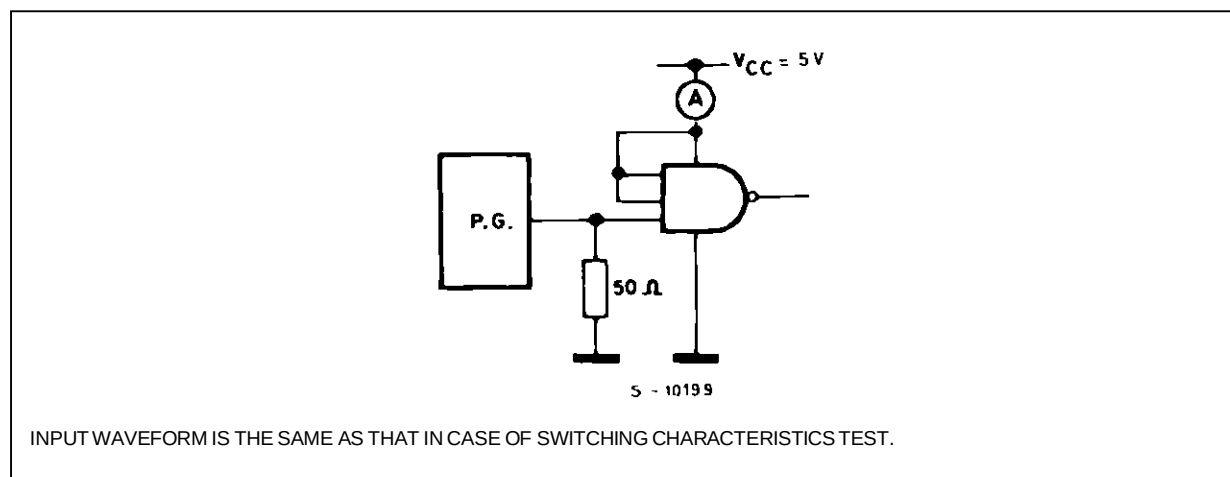
Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	4.5			8	15		19		22	
t _{PLH} t _{PHL}	Propagation Delay Time	4.5			14	22		28		33	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				46						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/3$ (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT



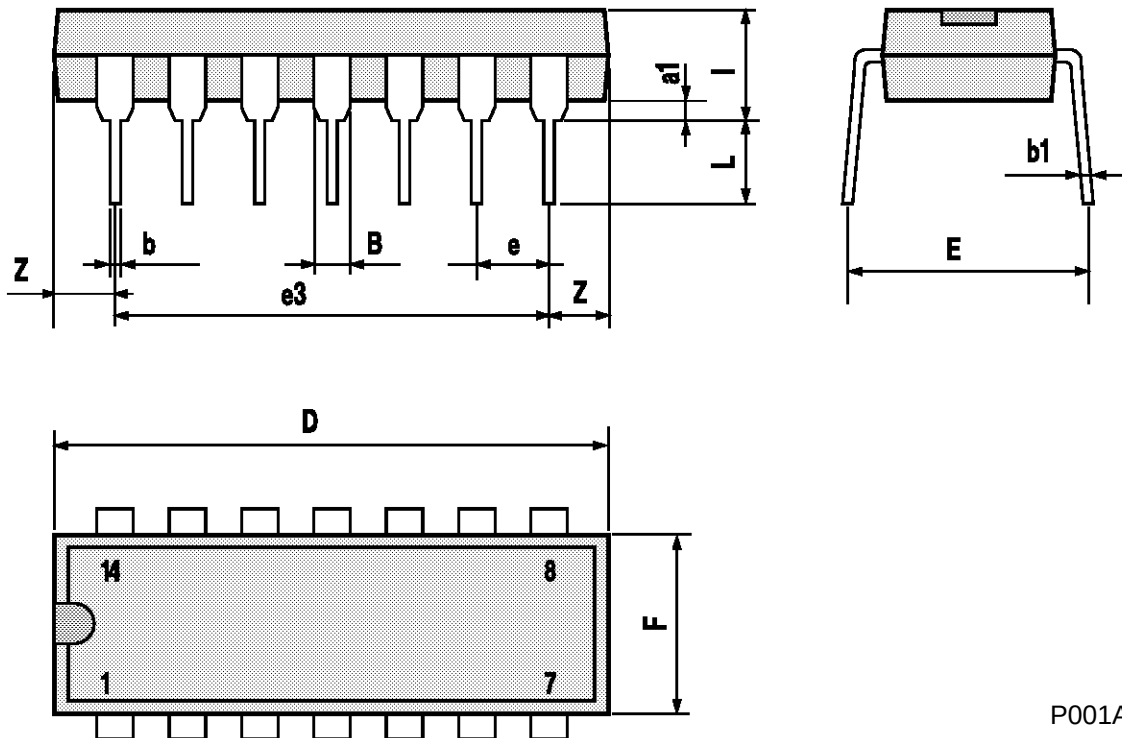
TEST CIRCUIT I_{CC} (Opr.)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

Plastic DIP14 MECHANICAL DATA

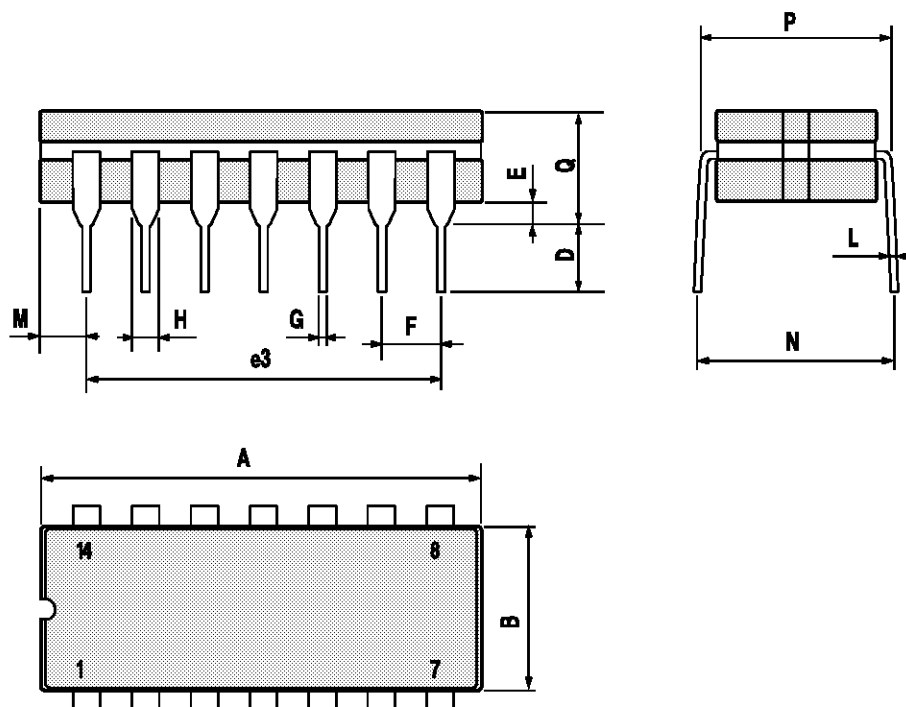
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

Ceramic DIP14/1 MECHANICAL DATA

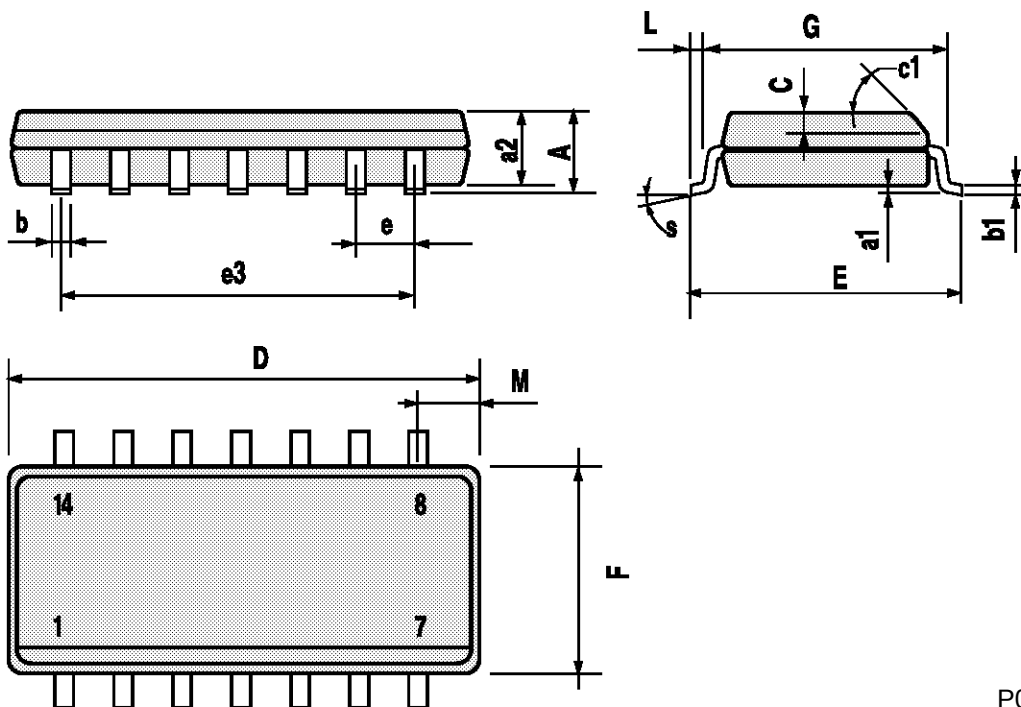
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

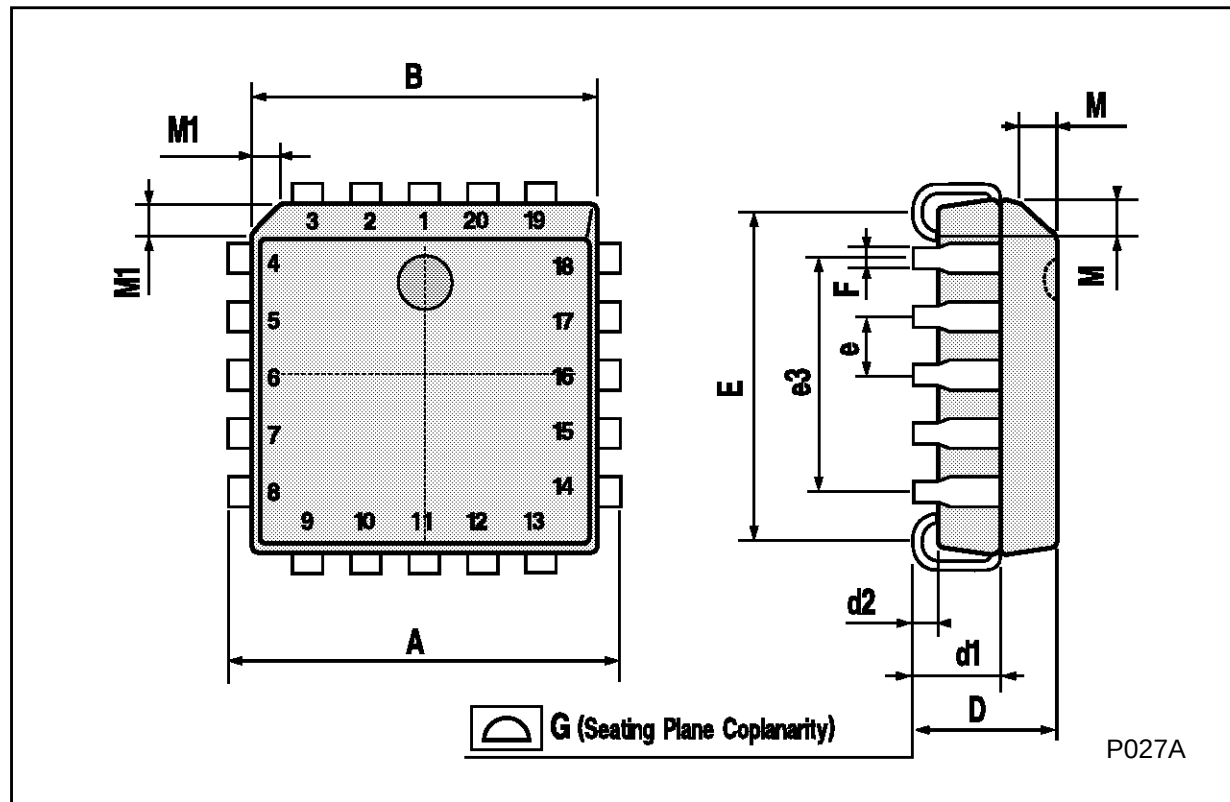
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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